

isc Silicon NPN Power Transistor

2SC2750

DESCRIPTION

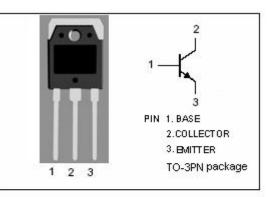
- Collector-Emitter Sustaining Voltage-
- : V_{CEO(SUS)}= 100V(Min)
- High Current Capability
- High Power Dissipation
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

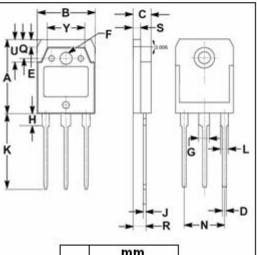
APPLICATIONS

• Designed for high speed, high current switching industrial applications.

ABSOLUTE MAXIMUM RATINGS(Ta=25°C)				
SYMBOL	OL PARAMETER VALUE		UNIT	
V _{CBO}	Collector-Base Voltage	150	V	
V _{CEO}	Collector-Emitter Voltage	100	V	
V_{EBO}	Emitter-Base Voltage	7	V	
lc	Collector Current-Continuous	15	A	
I _{CM}	Collector Current-Peak	30	A	
I _B	Base Current-Continuous	5	A	
Pc	Collector Power Dissipation @ Tc=25℃	100	W	
TJ	Junction Temperature	150	°C	
T _{stg}	Storage Temperature Range	-55~150	°C	

ABSOLUTE MAXIMUM RATINGS(Ta=25°C)





	mm		
DIM	MIN	MAX	
Α	19.60	20.10	
В	15.50	15.70	
С	4.70	4.90	
D	0.90	1.10	
E	1.90	2.10	
F	3.40	3.60	
G	2.90	3.20	
Н	3.20	3.40	
J	0.595	0.605	
Κ	20.00	20.70	
L	1.90	2.20	
N	10.89	10.91	
Q	4.90	5.10	
R	3.35	3.45	
S	1.995	2.100	
U	5.90	6.10	
Y	9.90	10.10	

isc website: <u>www.iscsemi.com</u>



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ELECTRICAL CHARACTERISTICS

$T_{c}\text{=}25^{\circ}\!\!\!\mathrm{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEO(SUS)}	Collector-Emitter Sustaining Voltage	I _C = 50mA; I _{B1} = 0	100			V
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = 10A; I _B = 1A			0.6	V
V _{BE(sat)}	Base-Emitter Saturation Voltage	I _C = 10A; I _B = 1A			1.5	V
І _{сво}	Collector Cutoff Current	V _{CB} = 100V; I _E = 0			10	μA
I _{CER}	Collector Cutoff Current	V _{CE} = 100V; R _{BE} = 50 Ω ; T _a = 125 ℃			1.0	mA
I _{CEX}	Collector Cutoff Current	V _{CE} = 100V;V _{BE(off)} = -1.5V; V _{CE} = 100V;V _{BE(off)} = -1.5V;T _a =125°C			10 500	μA
I _{EBO}	Emitter Cutoff Current	V _{EB} = 5V; I _C = 0			10	μA
h _{FE-1}	DC Current Gain	I _C = 5A; V _{CE} = 5V	30		120	
h _{FE-2}	DC Current Gain	I _C = 10A; V _{CE} = 5V	20			

Switching Times

ton	Turn-on Time			1.0	μ S
t _{stg}	Storage Time	I _C = 10A, I _{B1} = -I _{B2} = 1A, V _{CC} ≈ 50V; R _L = 5 Ω		1.5	μ S
t _f	Fall Time			0.3	μ S

h_{FE-1} Classifications

М	L	К
30-60	40-80	60-120

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